ABSTRACT OF THE DISCLOSURE

A method of promoting crystalline performance of a region of irradiating laser beam by a plurality of times is provided. A first crystalline region is formed by subjecting a portion of an amorphous semiconductor film to laser annealing by using laser beam having a wavelength in a range of 370 nm through 650 nm. It is preferable in carrying out laser annealing to irradiate laser beam after shaping the laser beam into linear beam having a shape at an irradiated face or a vicinity thereof in a linear shape by using an optical system. A second crystalline region is formed by subjecting a region including a portion of the first crystalline region to laser annealing. Crystalline performance of the first crystalline region formed as above, crystalline performance of the second crystalline region and crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same and a crystalline semiconductor film having excellent crystalline performance can be provided. When the crystalline semiconductor film constitutes an activation layer of TFT and electric properties of the TFT are measured, there are provided excellent properties having small dispersion.